

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing Of Claims:

1. (Currently Amended) A device for etching at least one of a substrate and a silicon body using an inductively coupled plasma, the device comprising:
 - an ICP source for generating a high-frequency electromagnetic alternating field;
 - a reactor for generating the inductively coupled plasma composed of reactive particles by an action of the high-frequency electromagnetic alternating field on a reactive gas; and
 - an arrangement for generating one of a static magnetic field and a time-variable magnetic field between the ICP source and the at least one of the substrate and the silicon body, the arrangement having at least two magnetic field coils arranged one above the other, wherein the at least two magnetic field coils are adapted to create a nearly field-free drift zone in between the at least two magnetic coils inside the reactor.
2. (Original) The device of claim 1, wherein the at least two magnetic field coils surround the reactor in at least some areas between the ICP source and the at least one of the substrate and the silicon body.
3. (Original) The device of claim 2, wherein a wall of the reactor is formed at least in some areas by at least one spacer associated with the at least two magnetic field coils.
4. (Original) The device of claim 1, wherein at least one component magnetic field generated by the at least two magnetic field coils is at least one of variable over time and pulsable by a power supply unit.
5. (Original) The device of claim 1, wherein electric currents flow through at least two of the at least two magnetic field coils in opposite directions.

6. (Original) The device of claim 1, wherein at least one of the static magnetic field, the time-variable magnetic field, a periodically variable magnetic field, and a pulsed magnetic field whose direction is at least approximately parallel to a direction defined by a tie line connecting the at least one of the substrate and the silicon body and the inductively coupled plasma is generatable using the at least two magnetic field coils.

7. (Original) The device of claim 1, wherein the at least one of the substrate and the silicon body is arrangeable symmetrically between the at least two magnetic field coils.

8. (Original) The device of claim 1, wherein the at least one of the substrate and the silicon body is arrangeable in one of a lower area and an output area of one of the at least two magnetic field coils facing away from the inductively coupled plasma, and within a space defined by another one of the at least two magnetic field coils.

9. (Original) The device of claim 8, wherein a substrate electrode is connected to the at least one of the substrate and the silicon body, which is arrangeable so that it is exposed to a component magnetic field of the one of the at least two magnetic field coils facing away from the inductively coupled plasma.

10. - 19. (Canceled)

20. (Currently Amended) A device for etching at least one of a substrate and a silicon body using an inductively coupled plasma, the device comprising:

means for generating a high-frequency electromagnetic alternating field;

means for generating the inductively coupled plasma composed of reactive particles by an action of the high-frequency electromagnetic alternating field on a reactive gas; and

means for generating one of a static magnetic field and a time-variable magnetic field between the means for generating the high-frequency electromagnetic field and the at least one of the substrate and the silicon body by using at least two magnetic field coils arranged one above the other, wherein the at least two magnetic field coils are adapted to create a nearly field-free drift zone in between the at least two magnetic field coils inside the reactor.

21. (New) The device of claim 1, wherein:
the reactor is adapted to accommodate the at least one of the substrate and the silicon body.
22. (New) The device of claim 20, wherein:
the means for generating the inductively coupled plasma is adapted to accommodate the at least one of the substrate and the silicon body.